

SANYO	No.3790	2SC4411
		PNP Epitaxial Planar Silicon Transistor Very High-Definition CRT Display Video Output Applications

Applications

- Wide-band amp.

Features

- High f_T ($f_T = 1.2\text{GHz}$ typ).
- High breakdown voltage ($V_{CBO} = 100\text{V}, V_{CEO} = 80\text{V}$).
- Large current ($I_C = 500\text{mA}$).
- Small reverse transfer capacitance ($C_{re} = 3.8\text{pF}/V_{CB} = 30\text{V}$).
- Adoption of FBET process.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CBO}	100	V
Collector-to-Emitter Voltage	V_{CEO}	80	V
Emitter-to-Base Voltage	V_{EBO}	3	V
Collector Current	I_C	500	mA
Collector Current (Pulse)	I_{CP}	1.0	A
Collector Dissipation	P_C	1.75	W
		15	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

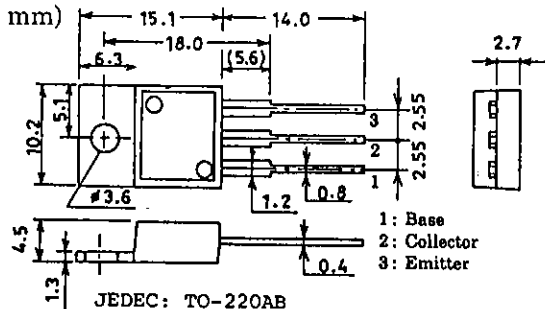
$T_c = 25^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

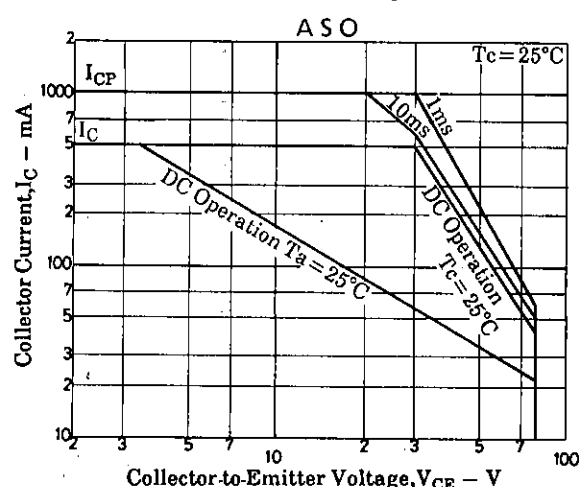
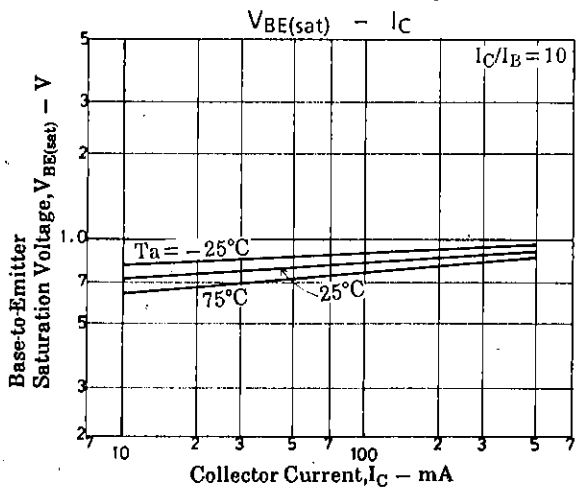
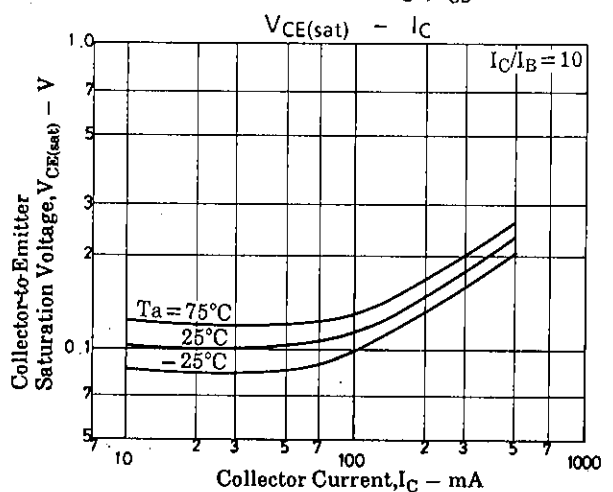
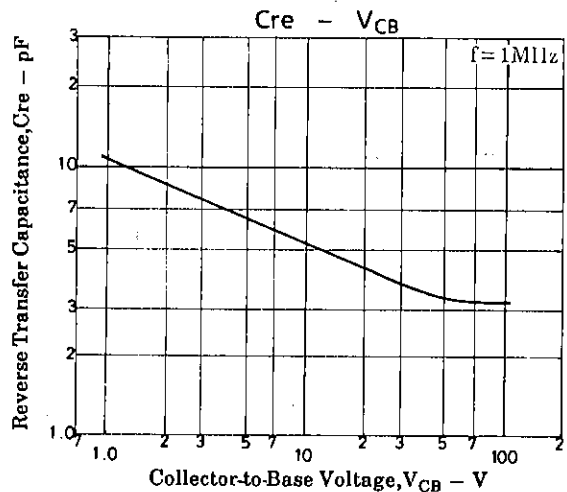
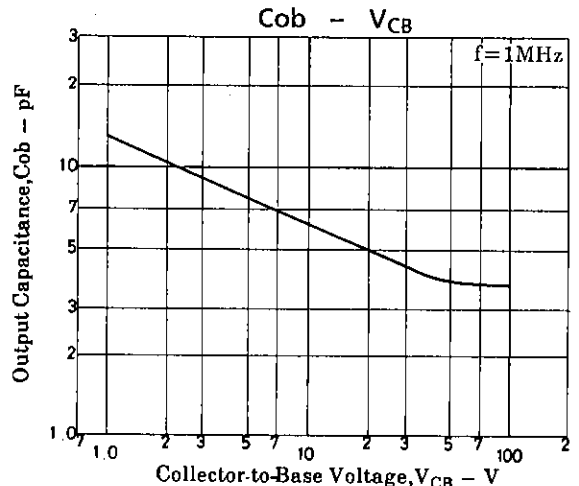
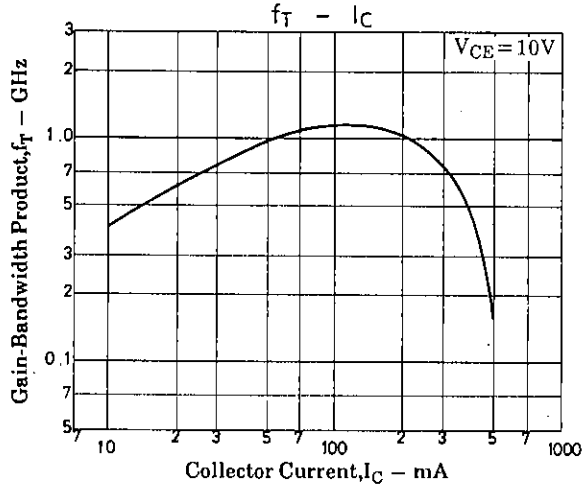
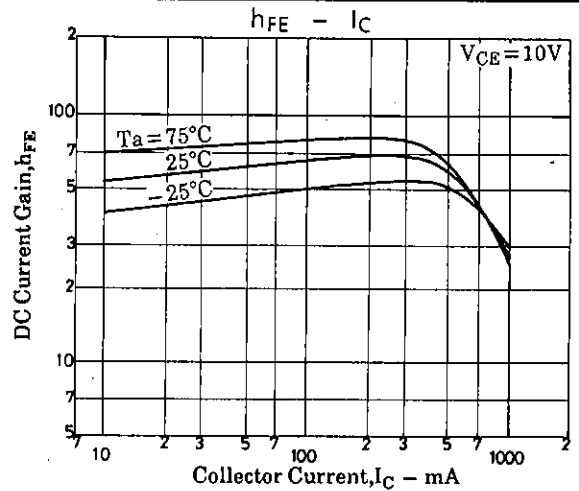
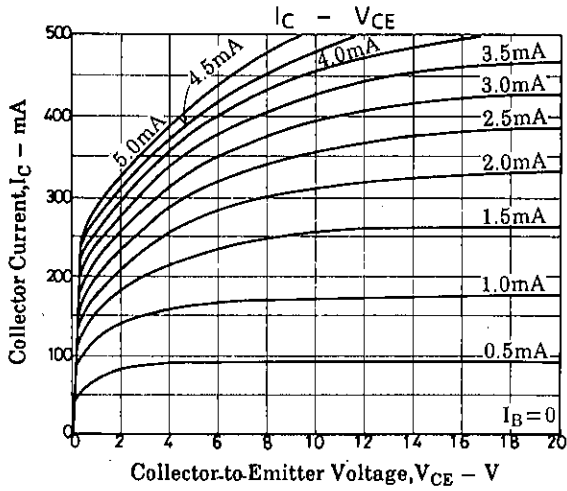
		min	typ	max	unit
Collector Cutoff Current	I_{CBO}			0.1	μA
Emitter Cutoff Current	I_{EBO}			5.0	μA
DC Current Gain	$h_{FE(1)}$	30		200	
	$h_{FE(2)}$	20			
Gain-Bandwidth Product	f_T		1.2		GHz
Output Capacitance	C_{ob}		4.4		pF
Reverse Transfer Capacitance	C_{re}		3.8		pF
C-E Saturation Voltage	$V_{CE(sat)}$			0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$			1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	100			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	80			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	3			V

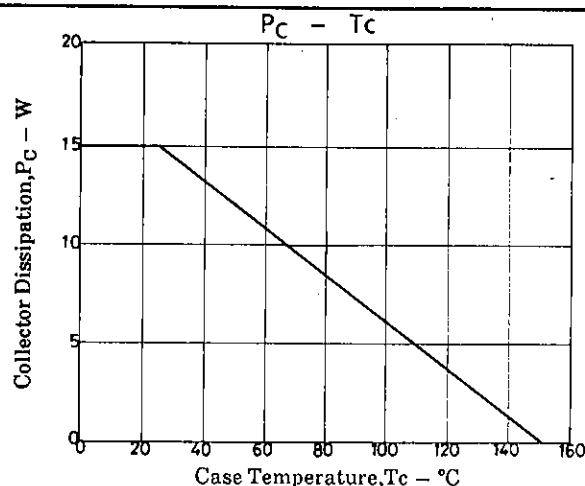
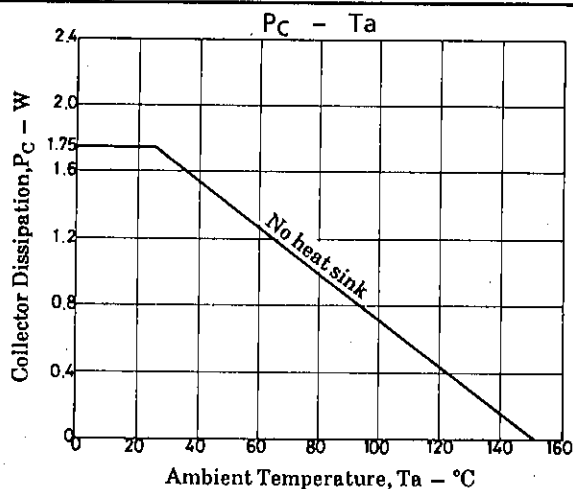
Package Dimensions 2010C

(unit: mm)



JEDEC: TO-220AB
EIAJ: SC-46





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